

Silicon NPN Power Transistors

2SD1175

DESCRIPTION

- With TO-3 package
- Built-in damper diode
- High voltage ,high power dissipation
- Wide area of safe operation

APPLICATIONS

- Line-operated horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

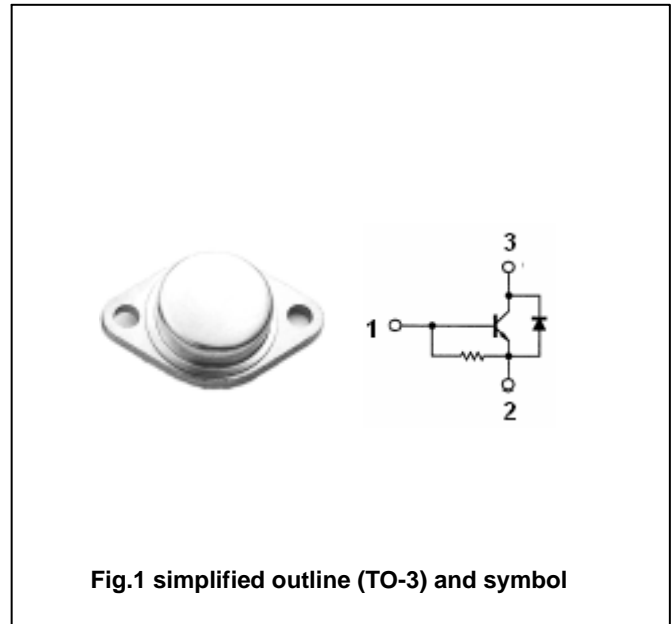


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	1500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		5	A
P_T	Total power dissipation	$T_C=25$	100	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-65~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =500mA; I _C =0;	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =4.0 A; I _B =0.8 A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =4.0 A; I _B =0.8 A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			50	μ A
		V _{CB} =1500V; I _E =0			1.0	mA
h _{FE-1}	DC current gain	I _C =1A ; V _{CE} =5V	10		30	
h _{FE-2}	DC current gain	I _C =4A ; V _{CE} =10V	5			
V _F	Diode forward voltage	I _F =4A			2.5	V

PACKAGE OUTLINE

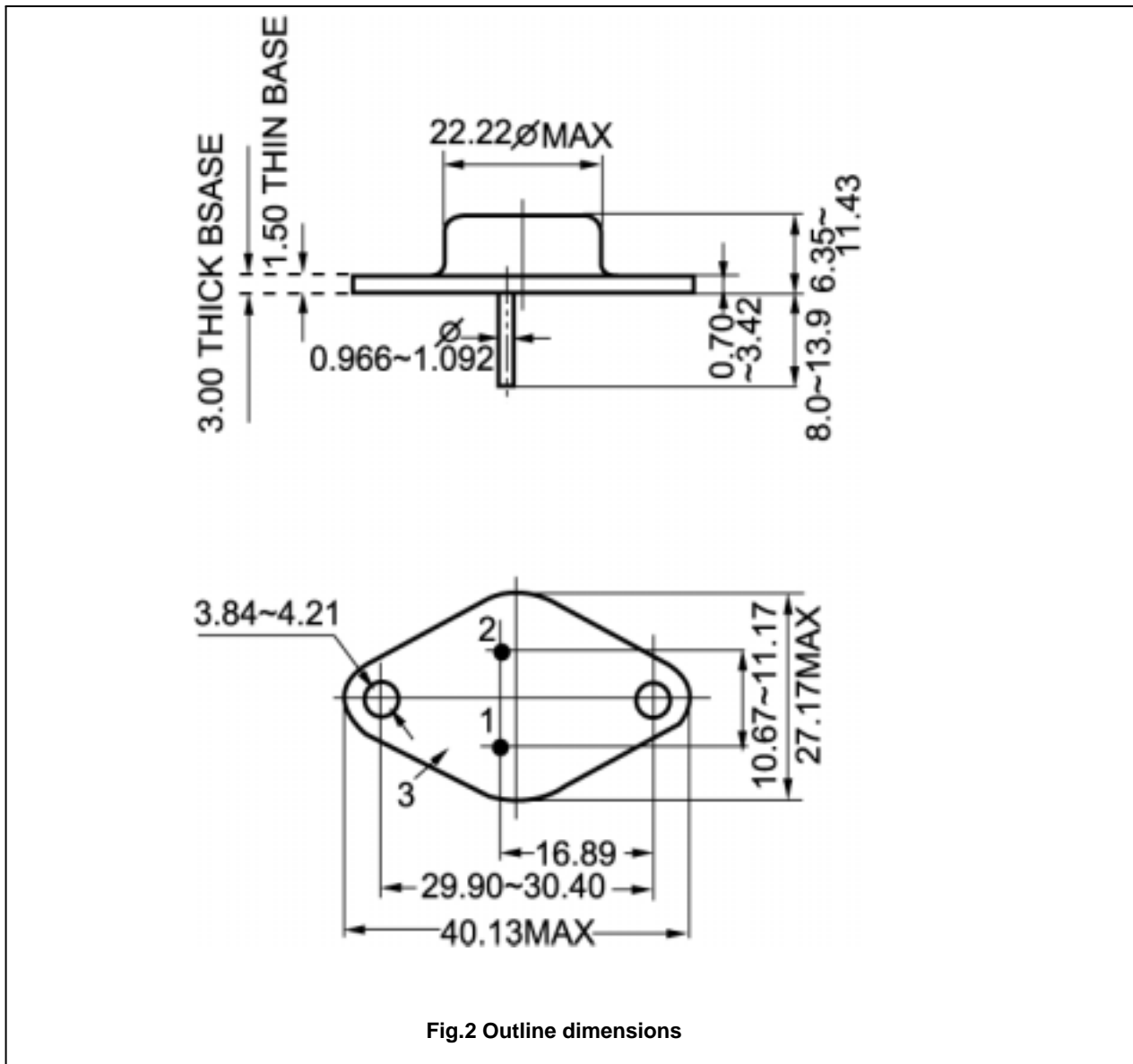


Fig.2 Outline dimensions